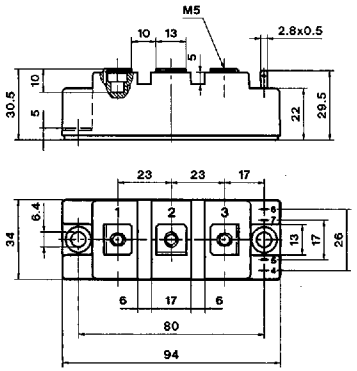
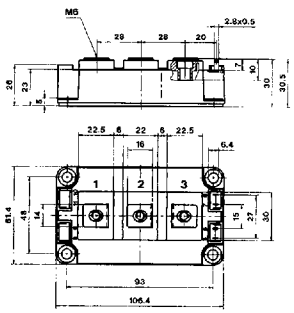
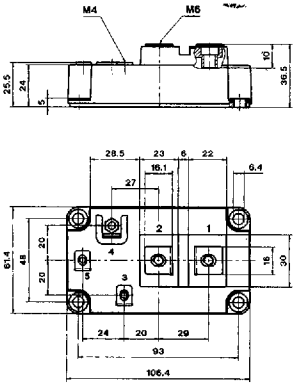
Cases D 61 ... 64 **SEMITRANS® 2**
L = 2 x 23 mm



Cases D 56 ... 58 **SEMITRANS® 3**
L = 2 x 28 mm
Low inductance L_{CE} < 20 nH

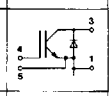
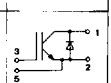
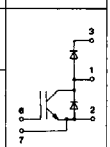
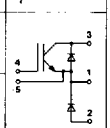
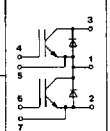
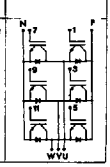


Cases D 59 ... 60 **SEMITRANS® 4** [6]
Low inductance L_{CE} < 20 nH



Section 6:
SEMITRANS® IGBT Modules; New Range 1995/96

3rd Version: Low Inductance, lower V_{CEsat}, soft and fast CAL diodes[1]; Preliminary Data [4]

Type [2]	V_{CES} [2]	I_C @ T_{case} =25°C	V_{CEsat} @ I_C 25°C typ.	P_{tot} @ [4] T_{case} 25°C	R_{thjc} [4] IGBT	R_{thCH} Modul	Case	Circuit
* under development	V	A	V	W	°C/W	°C/W		
SKM 50 GA 123 D	1200	50	3,2	310	0,4	0,05	D64	
SKM 75 GA 163 D	1600	75	3,8	500	0,25	0,05	D64	
SKM 100 GA 123 D	1200	100	3,2	625	0,20	0,05	D64	
SKM 100 GA 163 D	1600	100	3,8	625	0,20	0,05	D64	
SKM 200 GA 123 D	1200	200	3,2	1250	0,10	0,038	D59	
SKM 300 GA 123 D	1200	300	3,2	1550	0,08	0,038	D59	
SKM 300 GA 163 D	1600	300	3,8	1750	0,07	0,038	D59	
SKM 300 GA 173 D [3]	1700	300	3,8	1750	0,07	0,038	D59	
SKM 400 GA 123 D [5]	1200	400	3,2	2500	0,05	0,038	D59	
SKM 400 GA 163 D [5]	1600	400	3,9	2500	0,05	0,038	D59	
SKM 400 GA 173 D [3]	1700	400	3,9	2500	0,05	0,038	D59	
* SKM 500 GA 123 DS	1200	520	3,2	2700	0,045	0,038	D60	
SKM 75 GAL 123 D	1200	75	3,2	400	0,30	0,05	D62	
SKM 100 GAL 123 D	1200	100	3,2	625	0,20	0,05	D62	
SKM 100 GAL 163 D	1600	100	3,8	625	0,20	0,05	D62	
SKM 150 GAL 123 D	1200	150	3,2	800	0,16	0,038	D57	
SKM 200 GAL 123 D	1200	200	3,2	1120	0,10	0,038	D57	
SKM 200 GAL 163 D	1600	200	3,9	1120	0,10	0,038	D57	
SKM 75 GAR 123 D	1200	75	3,2	400	0,30	0,05	D63	
SKM 100 GAR 123 D	1200	100	3,2	625	0,20	0,05	D63	
SKM 100 GAR 163 D	1600	100	3,8	625	0,20	0,05	D63	
SKM 150 GAR 123 D	1200	150	3,2	800	0,16	0,038	D58	
SKM 200 GAR 123 D	1200	200	3,2	1120	0,10	0,038	D58	
SKM 200 GAR 163 D	1600	200	3,9	1120	0,10	0,038	D58	
SKM 50 GB 123 D	1200	50	3,2	310	0,4	0,05	D61	
SKM 75 GB 123 D	1200	75	3,2	400	0,30	0,05	D61	
SKM 75 GB 163 D	1600	75	3,8	500	0,25	0,05	D61	
SKM 75 GB 173 D [3]	1700	75	3,8	500	0,25	0,05	D61	
SKM 100 GB 123 D	1200	100	3,2	625	0,20	0,05	D61	
SKM 100 GB 163 D	1600	100	3,9	625	0,20	0,05	D61	
SKM 100 GB 173 D [3]	1700	100	3,9	625	0,20	0,05	D61	
* SKM 145 GB 123 D	1200	150	3,2	700	0,18	0,05	D61	
SKM 150 GB 123 D	1200	150	3,2	800	0,16	0,038	D56	
SKM 150 GB 163 D	1600	150	3,8	1000	0,13	0,038	D56	
SKM 150 GB 173 D [3]	1700	150	3,8	1000	0,13	0,038	D56	
SKM 200 GB 123 D [5]	1200	200	3,2	1250	0,10	0,038	D56	
SKM 200 GB 163 D	1600	200	3,9	1250	0,10	0,038	D56	
SKM 200 GB 173 D [3]	1700	200	3,9	1250	0,10	0,038	D56	
* SKM 300 GB 123 D	1200	300	3,2	1400	0,09	0,038	D56	
							page 6	
SKM 22 GD 123 D	1200	22	3,2	145	0,86	0,05	D28	
SKM 40 GD 123 D	1200	40	3,3	200	0,60	0,05	D28	
* SKM 75 GD 123 D	1200	75	3,2	400	0,30	0,05	D28	

1) CAL = Controlled Axial Lifetime Technology
2) 1600 V and 1700 V IGBTs have V_{isol} = 4 kV_{rms}/1 min
3) 1700 V types will replace 1600 V types in 1996
4) All data apply to one single IGBT element
5) Option enlarged diode, add suffix "1"
6) Option collector sense, add suffix "S" = case 60